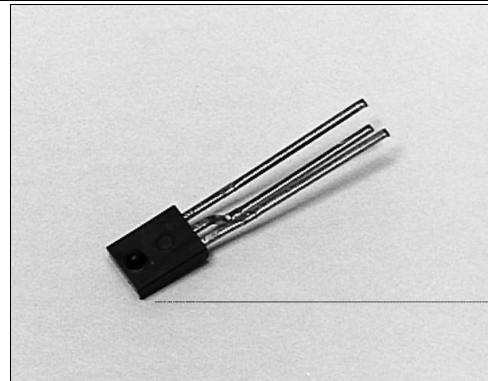


SDP86XX

Optoschmitt Detector

FEATURES

- Side-looking plastic package
- 55° (nominal) acceptance angle
- Wide sensitivity ranges
- TTL/LSTTL/CMOS compatible
- Buffer (SDP8600/8601/8602) or inverting (SDP8610/8611/8612) logic available
- Three different lead spacing arrangements
- Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes



INFRA-6.TIF

DESCRIPTION

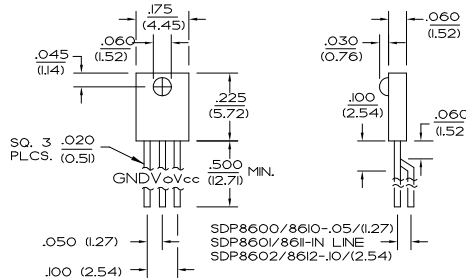
The SDP86XX series is a family of single chip Optoschmitt IC detectors molded in a side-looking black plastic package to minimize the effect of visible ambient light. The photodetector consists of a photodiode, amplifier, voltage regulator, Schmitt trigger and an NPN output transistor with a 10 k Ω (nominal) pull-up resistor. Output rise and fall times are independent of the rate of change of incident light. Detector sensitivity has been internally temperature compensated. Flexibility of use is enhanced by a choice of three different lead configurations; in-line (SDP8601/8611), 0.05 in. (1.27 mm) offset pin circle (SDP8600/8610) and 0.10 in. (2.54 mm) offset center lead (SDP8602/8612).

Device Polarity:

- Buffer - Output is HI when incident light intensity is above the turn-on threshold level.
- Inverter - Output is LO when incident light intensity is above the turn-on threshold level.

OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals	$\pm 0.005(0.12)$
	2 plc decimals	$\pm 0.020(0.51)$



DIM_028.cdr

SDP86XX

Optoschmitt Detector

ELECTRICAL CHARACTERISTICS (-40°C to +85°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Operating Supply Voltage	V _{CC}	4.5	12.0		V	T _A =25°C
Turn-on Threshold Irradiance	E _{ET(+)}				mW/cm ²	V _{CC} =5 V T _A =25°C (2)
SDP86XX-001			2.5			
SDP86XX-002			1.2			
SDP86XX-003			0.6			
Hysteresis (3)	HYST	5	30		%	
Supply Current	I _{CC}				mA	E _e =0 Or 3.0 mW/cm ² V _{CC} =5 V V _{CC} =12 V
High Level Output Voltage	V _{OH}				V	V _{CC} =5 V, I _{OH} =0 E _e =3.0 mW/cm ² E _e =0
SDP8600/8601/8602		2.4				
SDP8610/8611/8612		2.4				
Low Level Output Voltage	V _{OL}				V	V _{CC} =5 V, I _{OL} =12.8 mA E _e =0 E _e =3.0 mW/cm ²
SDP8600/8601/8602			0.4			
SDP8610/8611/8612			0.4			
Internal Pull-Up Resistor	R _{INT}	5.0	10.0	20.0	kΩ	
Operate Point Temperature Coefficient	O _{PTC}		-0.76		%/°C	Emitter @ Constant Temperature
Output Rise Time	t _r		60		ns	R _L =390 Ω, C _L =50 pF
Output Fall Time	t _f		15		ns	R _L =390 Ω, C _L =50 pF
Propagation Delay, Low-High, High-Low	t _{PLH} , t _{PHL}		5.0		μs	R _L =390 Ω, C _L =50 pF
Clock Frequency				100	kHz	R _L =390 Ω, C _L =50 pF

Notes

1. It is recommended that a bypass capacitor, 0.1 μF typical, be added between V_{CC} and GND near the device in order to stabilize power supply line.
2. The radiation source is an IRED with a peak wavelength of 935 nm.
3. Hysteresis is defined as the difference between the operating and release threshold intensities, expressed as a percentage of the operate threshold intensity.

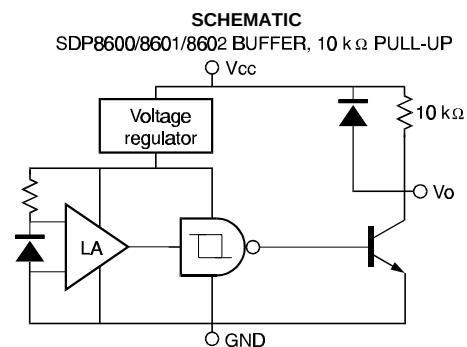
ABSOLUTE MAXIMUM RATINGS

(25°C Free-Air Temperature unless otherwise noted)

Supply Voltage	12 V (1)
Duration of Output	1.0 sec
Short to V _{CC} or Ground	18 mA
Output Current	18 mA
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C

Notes

1. Derate linearly from 25°C to 5.5 V at 85°C.



Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

Honeywell

SCHEMATIC

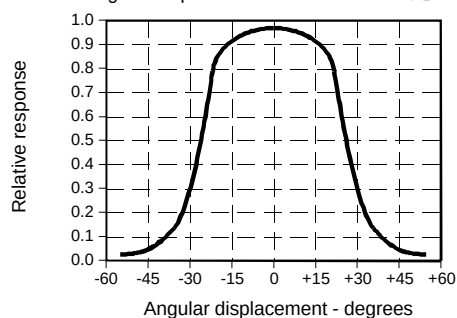
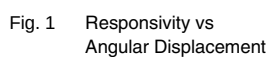
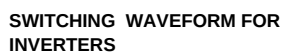
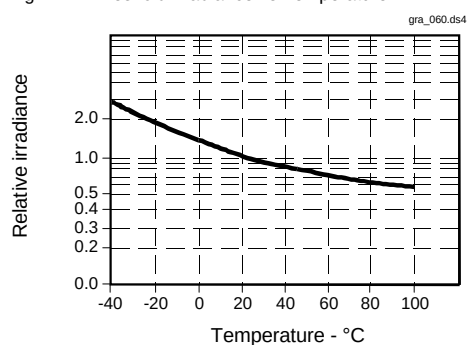


Fig. 2 Threshold Irradiance vs Temperature



SDP86XX

Optoschmitt Detector

Fig. 3 Output Rise Time (t_r) and Output Fall Time (t_f) vs Temperature

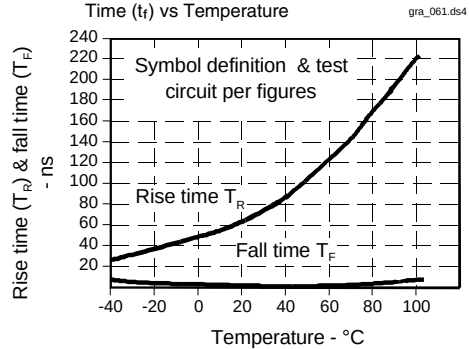


Fig. 4 Delay Time vs Temperature

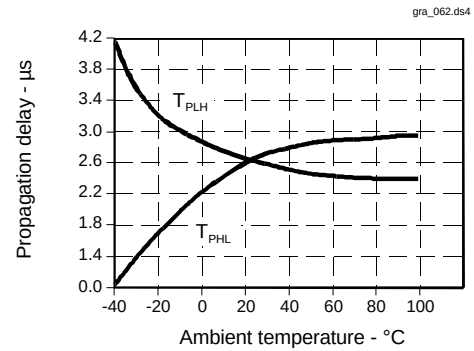
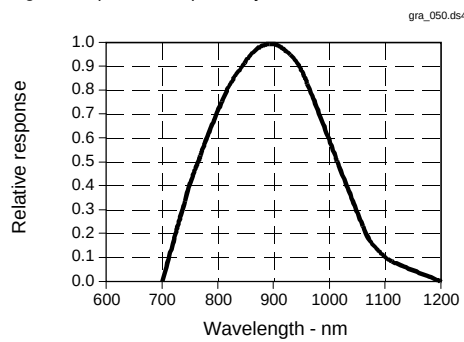


Fig. 5 Spectral Responsivity



All Performance Curves Show Typical Values